

# SIDC110D170H

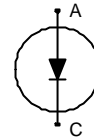
Fast switching diode chip in EMCON 3-Technology

**FEATURES:**

- 1700V EMCON 3 technology 200  $\mu\text{m}$  chip
- soft, fast switching
- low reverse recovery charge
- small temperature coefficient

**This chip is used for:**

- EUPEC power modules



**Applications:**

- resonant applications, drives

Chip Type	$V_R$	$I_F$	Die Size	Package	Ordering Code
SIDC110D170H	1700V	200A	10.5 x 10.5 mm <sup>2</sup>	sawn on foil	Q67050-A4179-A001

**MECHANICAL PARAMETER:**

Raster size	10.5 x 10.5	mm <sup>2</sup>
Area total / active	110.25 / 90.9	
Anode pad size	8.48 x 8.48	
Thickness	200	$\mu\text{m}$
Wafer size	150	mm
Flat position	180	deg
Max. possible chips per wafer	122 pcs	
Passivation frontside	Photoimide	
Anode metallization	3200 nm Al Si Cu	
Cathode metallization	Ni Ag –system suitable for epoxy and soft solder die bonding	
Die bond	electrically conductive glue or solder	
Wire bond	Al, $\leq 500\mu\text{m}$	
Reject Ink Dot Size	$\varnothing$ 0.65mm; max 1.2mm	
Recommended Storage Environment	store in original container, in dry nitrogen, < 6 month at an ambient temperature of 23°C	

**Maximum Ratings**

Parameter	Symbol	Condition	Value	Unit
Repetitive peak reverse voltage	$V_{RRM}$		1700	V
Continuous forward current limited by $T_{jmax}$	$I_F$		200	A
Single pulse forward current (depending on wire bond configuration)	$I_{FSM}$	$t_P = 10 \text{ ms sinusoidal}$	tbd	
Maximum repetitive forward current limited by $T_{jmax}$	$I_{FRM}$		400	
Operating junction and storage temperature	$T_j, T_{stg}$		-55...+150	°C

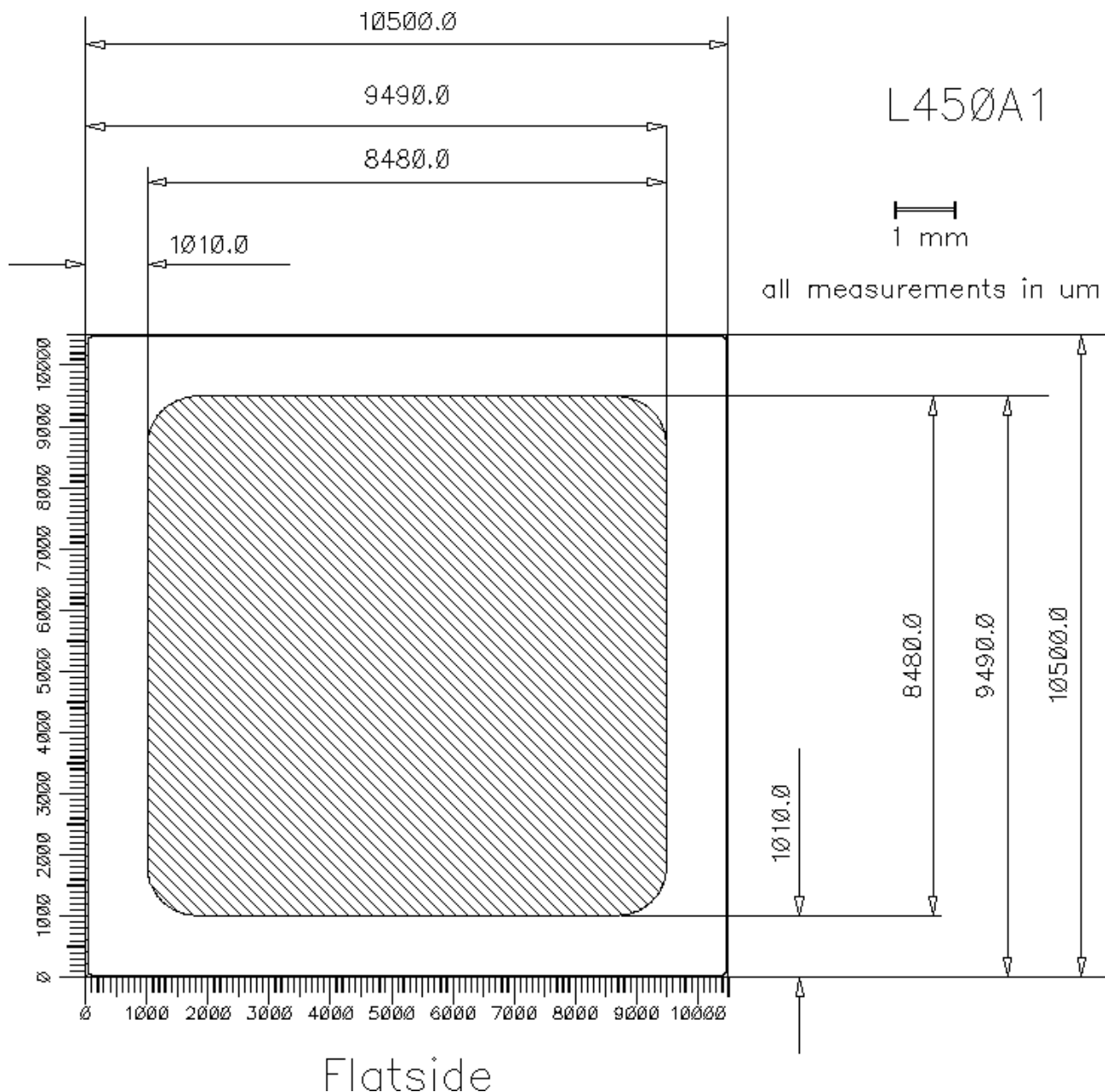
**Static Electrical Characteristics** (tested on chip),  $T_j=25^\circ\text{C}$ , unless otherwise specified

Parameter	Symbol	Conditions		Value			Unit
				min.	Typ.	max.	
Reverse leakage current	$I_R$	$V_R=1700\text{V}$	$T_j=25^\circ\text{C}$			250	$\mu\text{A}$
Cathode-Anode breakdown Voltage	$V_{Br}$	$I_R=0.25\text{mA}$	$T_j=25^\circ\text{C}$	1700			V
Forward voltage drop	$V_F$	$I_F=200\text{A}$	$T_j=25^\circ\text{C}$		1.8		V

**Dynamic Electrical Characteristics**, at  $T_j = 25^\circ\text{C}$ , unless otherwise specified, tested at component

Parameter	Symbol	Conditions		Value			Unit
				min.	Typ.	max.	
Reverse recovery time	$t_{rr1}$	$I_F=200\text{A}$	$T_j = 25^\circ\text{C}$		tbd		ns
	$t_{rr2}$	$di/dt=----\text{A/ms}$ $V_R=---\text{V}$	$T_j = 125^\circ\text{C}$				
Peak recovery current	$I_{RRM1}$	$I_F=200\text{A}$	$T_j = 25^\circ\text{C}$		tbd		A
	$I_{RRM2}$	$di/dt=----\text{A/ms}$ $V_R=---\text{V}$	$T_j = 125^\circ\text{C}$		tbd		
Reverse recovery charge	$Q_{rr1}$	$I_F=200\text{A}$	$T_j=25^\circ\text{C}$		tbd		$\mu\text{C}$
	$Q_{rr2}$	$di/dt=----\text{A/ms}$ $V_R=---\text{V}$	$T_j=125^\circ\text{C}$		tbd		
Peak rate of fall of reverse recovery current	$di_{rr1}/dt$	$I_F=200\text{A}$	$T_j=25^\circ\text{C}$		tbd		A/ $\mu\text{s}$
	$di_{rr2}/dt$	$di/dt=----\text{A/ms}$ $V_R=---\text{V}$	$T_j=125^\circ\text{C}$				
Softness	S1	$I_F=200\text{A}$	$T_j=25^\circ\text{C}$		tbd		1
	S2	$di/dt=----\text{A/ms}$ $V_R=---\text{V}$	$T_j=125^\circ\text{C}$				

**CHIP DRAWING:**





Preliminary

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**FURTHER ELECTRICAL CHARACTERISTICS:**

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This chip data sheet refers to the device data sheet

INFINEON TECHNOLOGIES /  
EUPEC

tbd

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**Description:**

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AQL 0,65 for visual inspection according to failure catalog

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Electrostatic Discharge Sensitive Device according to MIL-STD 883

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Test-Normen Villach/Prüffeld

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